

Rev.A Feb.-2024

TO-252 N MOS

N-CHANNEL MOSFET in a TO-252 Plastic Package.

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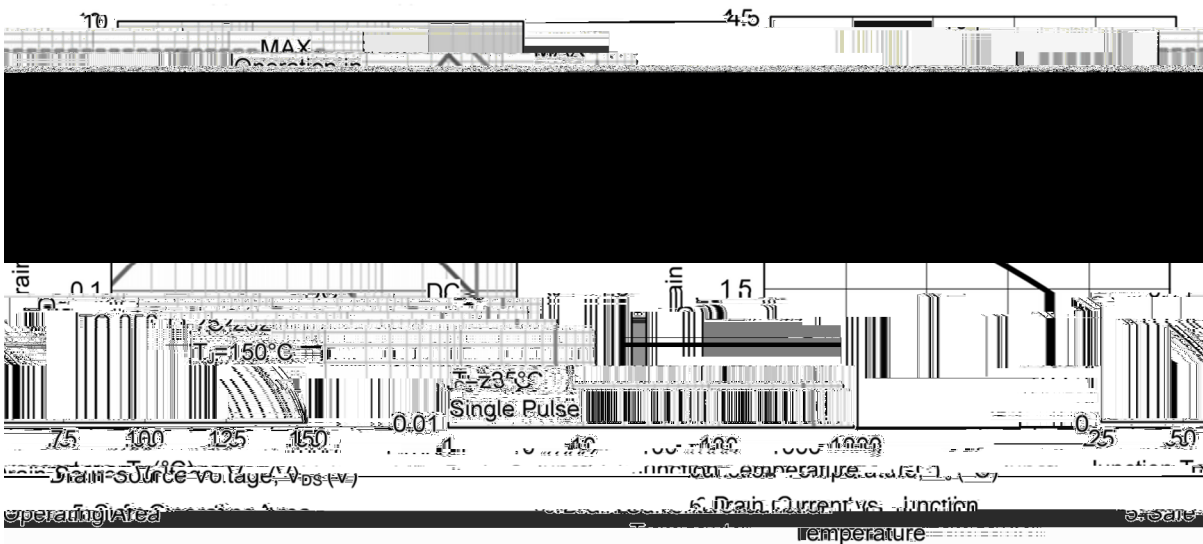
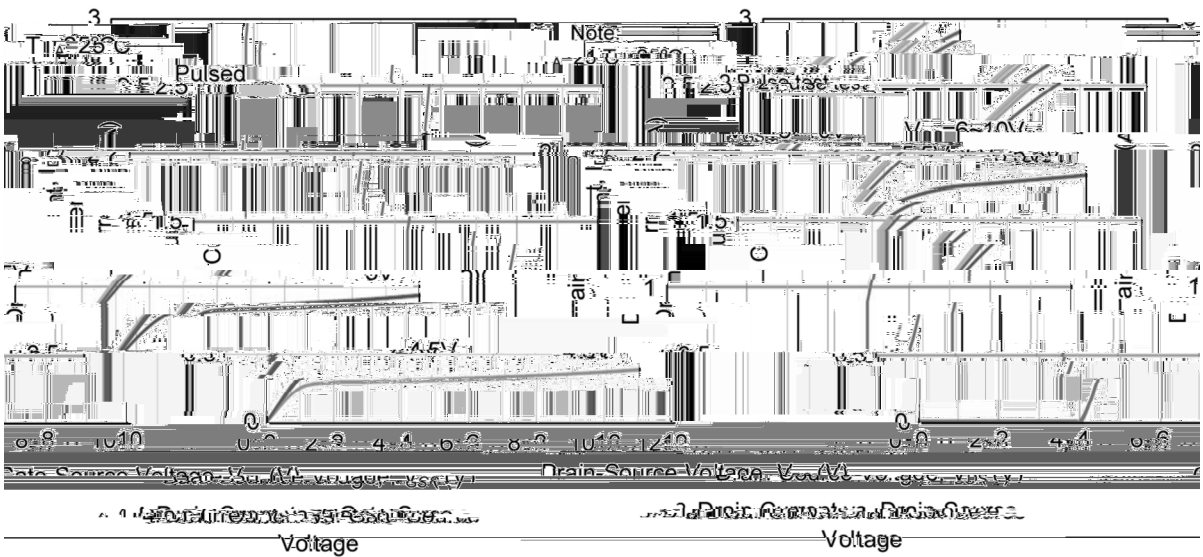
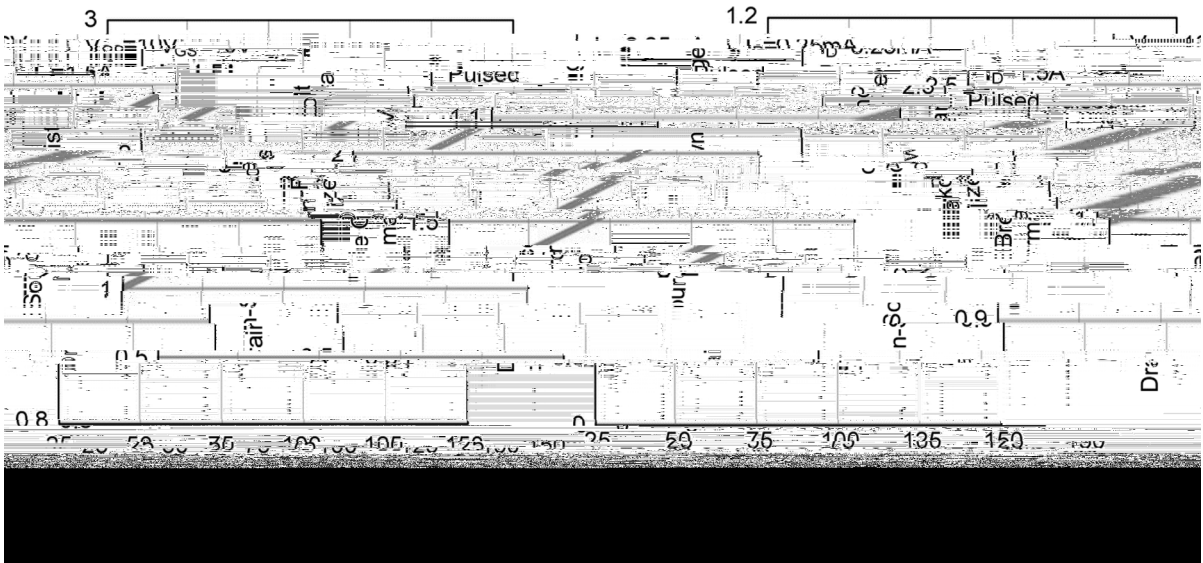
Low gate charge, low crss, fast switching, HF Product. Have good Electromagnetic Interference performance, HF Product.

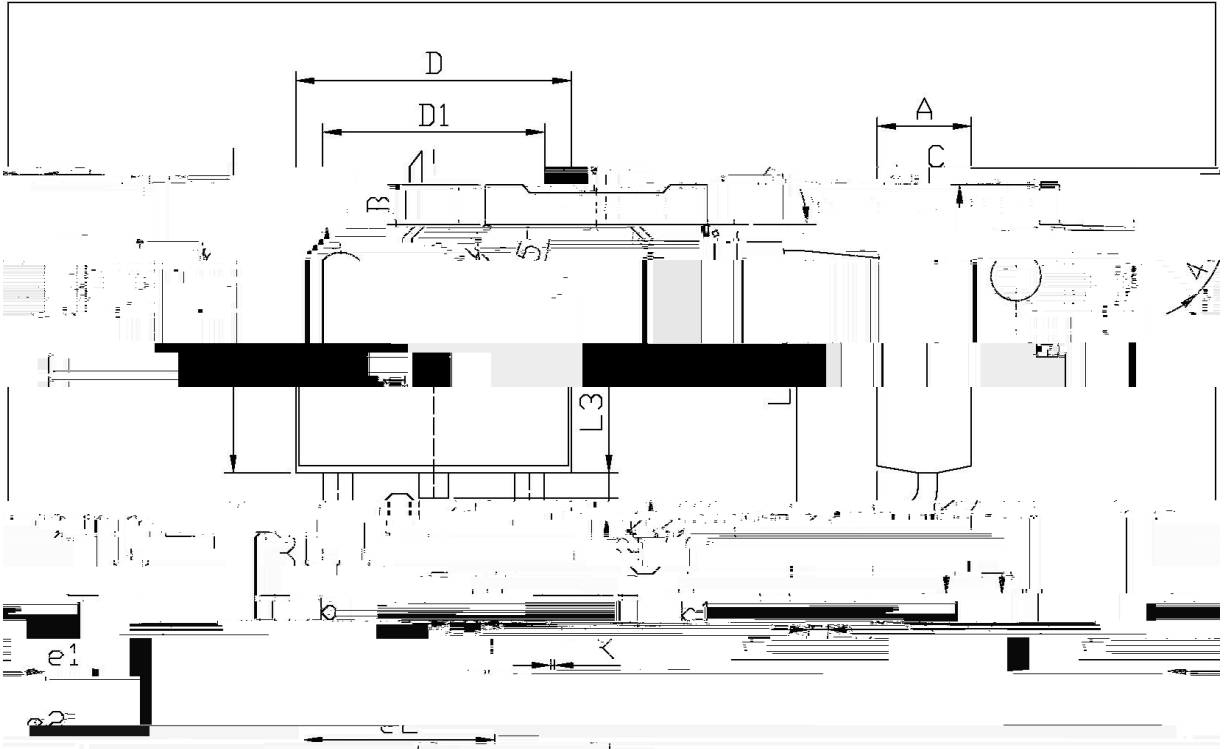
These devices are well suited for power switch circuit of adaptor and charger.

PIN1 G PIN 2 D PIN 3

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	500	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	3	A
Drain Current - Pulsed	I_{DM}	6	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	97	mJ
Avalanche Current	I_{AS}	4.4	A
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	45	W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	td(on)	V _{DD} =100V I _D =3.0A V _{GS} =10V R _G =25		4		ns

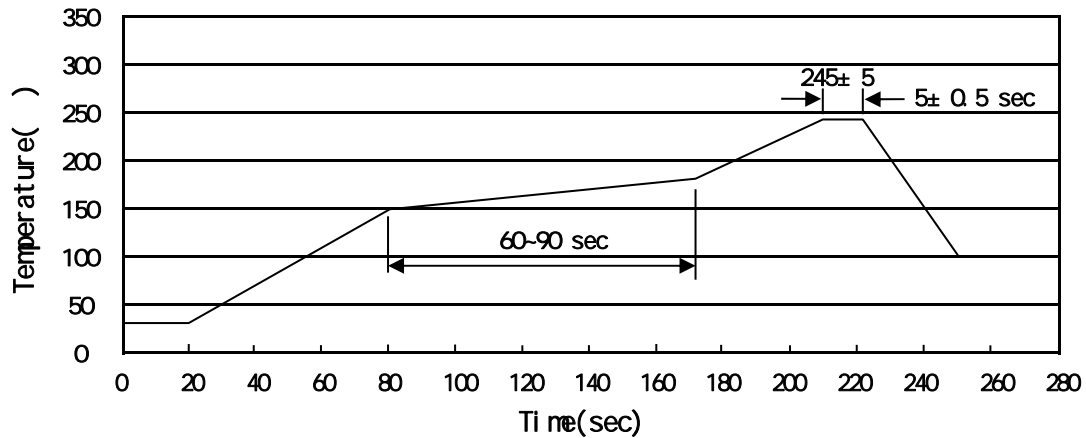




单位: mm

Dimensions In Millimeters		Dimensions In Millimeters		
Symbol	Max	Min	Symbol	Max
$2\phi 34$	0.00	0.10	$2\phi 21$	0.00
B	0.95	1.25	$e1$	0.00
h	0.45	0.55	$2\phi 21$	0.00
TR	0.60	0.60	$2\phi 21$	0.00
K	0.00	0.10	$D1$	5.10
				5.50

TQ-252

Temperature Profile for IR Reflow Soldering(Pb-Free)


Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	6	30,000	13 x16	360x360x50	380x335x366

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-251/252	75	48	3,600	5	18,000	526x20.5x5.25	555x164x50	575x290x180